


MITSUBISHI IGBT

CY25AAJ-8F

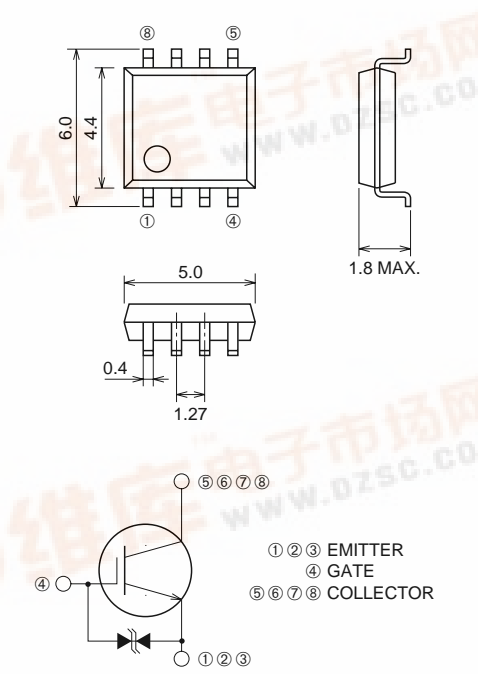
Nch IGBT for STROBE FLASHER

CY25AAJ-8F



- VCES 400V
- ICM 150A
- Drive voltage 4V

OUTLINE DRAWING Dimensions in mm



① ② ③ EMITTER
④ GATE
⑤ ⑥ ⑦ ⑧ COLLECTOR

SOP-8

APPLICATION

Strobe Flasher for camera

MAXIMUM RATINGS (Tc = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V _{CE} S	Collector-emitter voltage	V _{GE} = 0V	400	V
V _{GE} S	Gate-emitter voltage	V _{CE} = 0V	±6	V
V _{GEM}	Peak gate-emitter voltage	V _{CE} = 0V, t _w = 10s	±8	V
I _{CM}	Collector current (Pulsed)	C _M = 400μF see figure1	150	A
T _j	Junction temperature		-40 ~ +150	°C
T _{stg}	Storage temperature		-40 ~ +150	°C

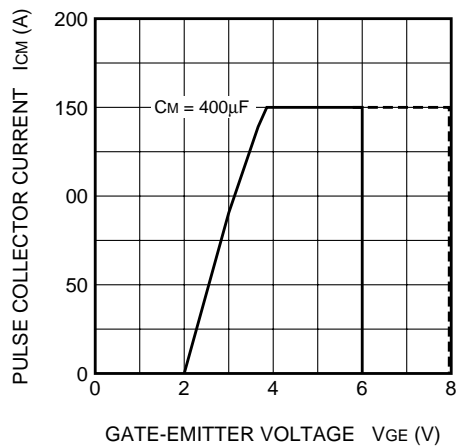
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ELECTRICAL CHARACTERISTICS ($T_j = 25^\circ\text{C}$)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) CES	Collector-emitter breakdown voltage	$I_C = 1\text{mA}, V_{GE} = 0\text{V}$	450	—	—	V
V (BR) GES	Gate-emitter breakdown voltage	$I_G = \pm 100\mu\text{A}, V_{CE} = 0\text{V}$	± 8	—	—	V
ICES	Collector-emitter leakage current	$V_{CE} = 400\text{V}, V_{GE} = 0\text{V}$	—	—	10	μA
IGES	Gate-emitter leakage current	$V_{GE} = \pm 6\text{V}, V_{CE} = 0\text{V}$	—	—	± 10	μA
VGE (th)	Gate-emitter threshold voltage	$V_{CE} = 10\text{V}, I_C = 1\text{mA}$	—	—	1.5	V

Figure1. MAXIMUM PULSE COLLECTOR CURRENT



APPLICATION EXAMPLE

